



RLT1060M-2WG

TECHNICAL DATA



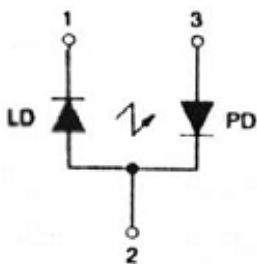
High Power Infrared Laser Diode

Lasing mode structure: **multi mode**
Lasing wavelength: **typ. 1060 nm**
Max. optical power: **1.3 W**
Package: **9 mm (SOT-148)**

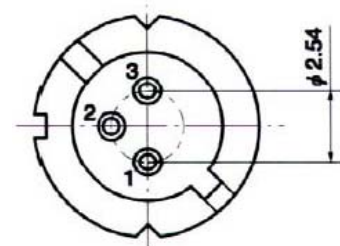
NOTE!
LASERDIODE
MUST BE COOLED!

ATTENTION
OBSERVE PRECAUTIONS
FOR HANDLING
ELECTROSTATIC SENSITIVE DEVICE

PIN CONNECTION:



- 1) Laserdiode cathode
- 2) Laserdiode anode and photodiode cathode
- 3) Photodiode anode



QTY: 2 Pcs

Wafer #: BIW-A1512Y-1060-100-0009C-C906-B409
Bar #: 101708-TO CAN-
Operator: DS

Chip #	Fit Ith (mA)	Fit Efficiency (mW/mA)	Current @1300mW (mA)	Voltage @1300mW (V)	Peak wavelength @1300mW (nm)	Center wavelength @1300mW (nm)	Peak width @1300mW (nm)	PD current @1300mW (mA)
6	327.476	0.807	1938.38	1.38	1056.44	1056.91	1.42	1.234
9	319.611	0.802	1940.56	1.39	1057.28	1057.35	1.34	1.392

Voltage measurement may not be accurate due to residual resistance in testing.

